Adilson S Cardoso

List of Publications by Year
in descending order

22	259	933447 10	940533 16
papers	citations	h-index	g-index

22	22	22	271
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	A 0.8 THz $f_{m MAX}$ SiGe HBT Operating at 4.3 K. IEEE Electron Device Letters, 2014, 35, 151-153.	3.9	60
2	A New Wideband, Low Insertion Loss, High Linearity SiGe RF Switch. IEEE Microwave and Wireless Components Letters, 2020, 30, 985-988.	3.2	23
3	Single-Event Transient and Total Dose Response of Precision Voltage Reference Circuits Designed in a 90-nm SiGe BiCMOS Technology. IEEE Transactions on Nuclear Science, 2014, 61, 3210-3217.	2.0	22
4	An Investigation of Single-Event Effects and Potential SEU Mitigation Strategies in Fourth-Generation, 90Ânm SiGe BiCMOS. IEEE Transactions on Nuclear Science, 2013, 60, 4175-4183.	2.0	20
5	An Investigation of Single Event Transient Response in 45-nm and 32-nm SOI RF-CMOS Devices and Circuits. IEEE Transactions on Nuclear Science, 2013, 60, 4405-4411.	2.0	18
6	Evaluation of Enhanced Low Dose Rate Sensitivity in Fourth-Generation SiGe HBTs. IEEE Transactions on Nuclear Science, 2014, 61, 2915-2922.	2.0	18
7	An Investigation of Single-Event Transients in C-SiGe HBT on SOI Current Mirror Circuits. IEEE Transactions on Nuclear Science, 2014, 61, 3193-3200.	2.0	15
8	On the Transient Response of a Complementary (npn <formula formulatype="inline"><tex) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 Transactions on Nuclear Science, 2014, 61, 3146-3153.	2.0	15
9	Total Ionizing Dose Response of Triple-Well FET-Based Wideband, High-Isolation RF Switches in a 130 nm SiGe BiCMOS Technology. IEEE Transactions on Nuclear Science, 2013, 60, 2567-2573.	2.0	12
10	Single-Event Effects in a W-Band (75-110ÂGHz) Radar Down-Conversion Mixer Implemented in 90Ânm, 300ÂGHz SiGe HBT Technology. IEEE Transactions on Nuclear Science, 2015, 62, 2657-2665.	2.0	12
11	Impact of Total Ionizing Dose on a 4th Generation, 90Ânm SiGe HBT Gaussian Pulse Generator. IEEE Transactions on Nuclear Science, 2014, 61, 3050-3054.	2.0	10
12	A SiGe 8â€“18-GHz Receiver With Built-In-Testing Capability for Self-Healing Applications. IEEE Transactions on Microwave Theory and Techniques, 2014, 62, 2370-2380.	4.6	10
13	On the Cryogenic RF Linearity of SiGe HBTs in a Fourth-Generation 90-nm SiGe BiCMOS Technology. IEEE Transactions on Electron Devices, 2015, 62, 1127-1135.	3.0	5
14	Total Ionizing Dose Effects on a High-Voltage (>30V) Complementary SiGe on SOI Technology. IEEE Transactions on Nuclear Science, 2017, 64, 277-284.	2.0	5
15	Design Methodology for a Wideband, Low Insertion Loss, Digital Step Attenuator in SiGe BiCMOS Technology. IEEE Transactions on Circuits and Systems II: Express Briefs, 2022, 69, 744-748.	3.0	5
16	Mitigation of Total Dose Performance Degradation in an 8â€“18ÂGHz SiGe Reconfigurable Receiver. IEEE Transactions on Nuclear Science, 2014, 61, 3226-3235.	2.0	4
17	On-die self-healing of mixer image-rejection ratio for mixed-signal electronic systems. , 2012, , .		1
18	An on-chip SiGe HBT characterization circuit for use in self-healing RF systems. , 2013, , .		1

#	Article	IF	Citations
19	On the cryogenic performance of ultra-low-loss, wideband SPDT RF switches designed in a 180 nm SOI-CMOS technology. , 2014, , .		1
20	An Investigation of the SET Response of Devices and Differential Pairs in a 32-nm SOI CMOS Technology. IEEE Transactions on Nuclear Science, 2015, 62, 2643-2649.	2.0	1
21	The Effects of Temperature on the Single-Event Transient Response of a High-Voltage (>30 V) Complementary SiGe-on-SOI Technology. IEEE Transactions on Nuclear Science, 2019, 66, 389-396.	2.0	1
22	Cryogenic Characterization of RF Low-Noise Amplifiers Utilizing Inverse-Mode SiGe HBTs for Extreme Environment Applications. IEEE Transactions on Device and Materials Reliability, 2018, 18, 613-619.	2.0	0